OPA8813QQF

Infrared LED Chip

High Speed / N Side-Up

GaAlAs/GaAlAs

1. Material

Substrate	GaAs	(P Type) Removed
Epitaxial Layer	GaAlAs	(N/P Type)

2. Electrode

N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

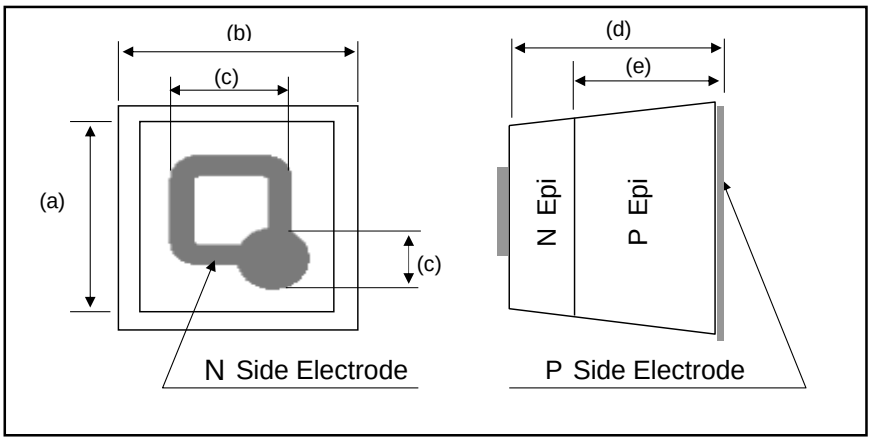
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F			2	V	IF=100mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	11			mW	IF=100mA
Wavelength	λ_P		885		nm	IF=50mA
	$\Delta\lambda$		80		nm	IF=50mA
Rise Time	Tr		700		ns	
Fall Time	Tf		400		ns	

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area	----------	12.0mil x 12.0mil
(b) Bottom Area	----------	13.0mil x 13.0mil
(c) Bonding Pad	----------	100um
(d) Chip Thickness	----------	9.0mil
(e) Junction Height	----------	4.0mil



AUK CORP.

Yakchon Factory, 62-21, 8, Yakchon-ro, Iksan, Korea

Tel. +82 63 839 1111 **Fax.** +82 63 835 8259

www.auk.co.kr

IATF16949 ISO14001